

# isc N-Channel MOSFET Transistor

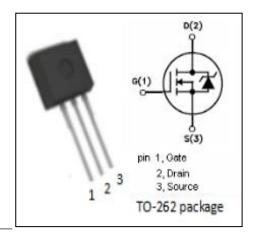
**IRFB3607** 

### • FEATURES

- Static drain-source on-resistance:
  R<sub>DS</sub>(on) ≤9.0mΩ
- Enhancement mode
- · Fast Switching Speed
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

### DESCRITION

• reliable device for use in a wide variety of applications

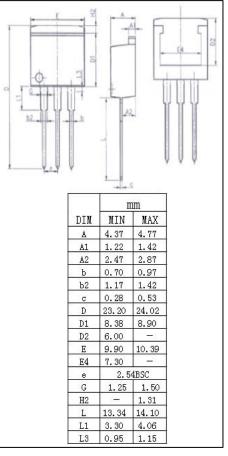


## • ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

SYMBOL	PARAMETER	VALUE	UNIT
$V_{DSS}$	Drain-Source Voltage	75	V
$V_{GS}$	Gate-Source Voltage	±20	V
I <sub>D</sub>	Drain Current-Continuous	80	А
I <sub>DM</sub>	Drain Current-Single Pulsed 3		А
$P_D$	Total Dissipation @T <sub>C</sub> =25°C	140	W
Тј	Max. Operating Junction Temperature	Operating Junction Temperature 175	
T <sub>stg</sub>	Storage Temperature	-55~175	$^{\circ}$

## • THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
Rth(ch-c)	Channel-to-case thermal resistance	1.045	°C/W





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#### **ELECTRICAL CHARACTERISTICS**

T<sub>C</sub>=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	ТҮР	MAX	UNIT
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V; ID =250 μ A	75			V
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> =V <sub>GS</sub> ; ID =100 μ A	2.0		4.0	V
R <sub>DS(on)</sub>	Drain-Source On-Resistance	V <sub>GS</sub> =10V; I <sub>D</sub> =46A			9.0	m Ω
lgss	Gate-Source Leakage Current	V <sub>GS</sub> =±20V			±0.1	μА
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> =75V; V <sub>GS</sub> = 0V			20	μА
V <sub>SD</sub>	Diode forward voltage	Is=46A, V <sub>GS</sub> = 0 V			1.3	V



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